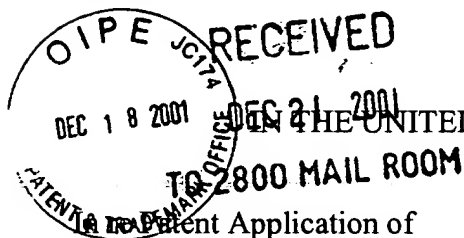


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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent Application of

Chih Hsin Wang

Application No. 09/916,619

Filed: July 26, 2001

For: SELF ALIGNED METHOD OF  
FORMING A SEMICONDUCTOR  
MEMORY ARRAY OF FLOATING  
GATE MEMORY CELLS WITH  
CONTROL GATE SPACERS, AND A  
MEMORY ARRAY MADE THEREBY

Group Art Unit: 2812

Examiner: Unknown

**PRELIMINARY AMENDMENT**

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Assistant Commissioner for Patents  
Washington, D.C. 20231

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited  
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Washington, DC 20231, on 12/4/ 2001.

GRAY CARY WARE & FREIDENRICH Date 12/4/01

By: \_\_\_\_\_

*Kathleen LaBrie*

Kathleen LaBrie

Sir:

Please preliminarily amend the above identified application as follows:

I. CLEAN VERSION OF AMENDED PARAGRAPHS

**Please substitute each of the following paragraphs for the cited paragraph in the  
application disclosure:**

Paragraph on page 12, lines 21-30:

Nitride spacers 36 are then formed along the surfaces of poly block 32 that face second  
trenches 35. Formation of spacers is well known in the art, and involves the deposition of a  
material over the contour of a structure, followed by an anisotropic etch process, whereby the  
material is removed from horizontal surfaces of the structure, while the material remains largely  
intact on vertically oriented surfaces of the structure. Thus, nitride spacer 36 formation is

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Cont